ON Semiconductor®

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N-Channel IGBT

600V, 20A, VCE(sat);1.45V Single TO-3PF-3L

Features

- IGBT V_{CE}(sat)=1.45V typ. (I_C=20A, V_{GE}=15V)
- IGBT t_f=67ns typ.
- Enhansment type

- Adaption of full isolation type package
- Maxium junction temperature Tj=175°C

Applications

• Power factor correction of white goods appliance

• General purpose inverter

Specifications

Absolute Maximum Ratings at Ta = 25°C, Unless otherwise specified

Parameter	Symbol	Conditions		Ratings	Unit
Collector to Emitter Voltage	VCES			600	٧
Gate to Emitter Voltage	V _{GES}			±20	٧
Collector Current (DC)	1-*4	Limited by Tjmax	@ Tc=25°C *2	40	Α
	IC*1		@ Tc=100°C *2	20	Α
Collector Current (Pulse)	lCP	Pulse width Limited by Tjmax		105	Α
Allowable Power Dissipation	PD	Tc=25°C (Our ideal heat dissipation condition) *2		64	W
Junction Temperature	Tj			175	°C
Storage Temperature	Tstg			- 55 to +175	°C

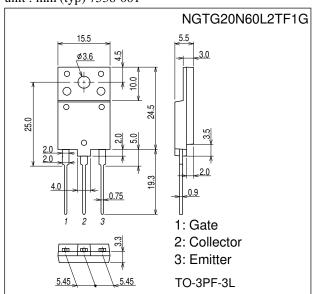
Note: *1 Collector Current is calculated from the following formula.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit: mm (typ) 7538-001

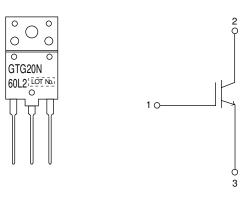


Ordering & Package Information

Device	Package	Shipping	note
NGTG20N60L2TF1G	TO-3PF-3L SC-94	30 pcs. / tube	Pb-Free

Marking

Electrical Connection



 $[\]overline{R_{th}}(j-c) \times V_{CE}(sat)(Tj, I_C(Tc))$ *2 Our condition is radiation from backside.

Electrical Characteristics at Ta = 25°C, Unless otherwise specified

Parameter	Symbol	Conditions		Ratings		Unit	
Parameter	Symbol			min	typ	max	Unit
Collector to Emitter Breakdown Voltage	V(BR)CES	I _C =500μA, V _{GE} =0V		600			٧
Collector to Emitter Cut off Current	ICES	V _{CE} =600V, V _{GE} =0V	Tc=25°C			10	μΑ
			Tc=150°C			1	mA
Gate to Emitter Leakage Current	IGES	V _{GE} =±20V, V _{CE} =0V				±100	nA
Gate to Emitter Threshold Voltage	V _{GE} (th)	V _{CE} =20V, I _C =250μA		4.5		6.5	V
Collector to Emitter Saturation Voltage	V _{CE} (sat)	V _{GE} =15V, I _C =20A	Tc=25°C		1.45	1.65	V
			Tc=150°C		1.8		V
Input Capacitance	Cies	V _{CE} =20V,f=1MHz			2000		pF
Output Capacitance	Coes				60		pF
Reverse Transfer Capacitance	Cres				50		pF
Turn-ON Delay Time	t _d (on)	V _{CC} =300V,I _C =20A R _G =30Ω,L=200μH V _{GE} =0V/15V Vclamp=400V See Fig.1, See Fig.2			60		ns
Rise Time	t _r				37		ns
Turn-ON Time	ton				400		ns
Turn-OFF Delay Time	t _d (off)				193		ns
Fall Time	tf				67		ns
Turn-OFF Time	toff				281		ns
Total Gate Charge	Qg	V _{CE} =300V, V _{GE} =15V, I _C =20A			84		nC
Gate to Emitter Charge	Qge				16		nC
Gate to Collector "Miller" Charge	Qgc				37		nC

Thermal Characteristics at Ta = 25°C, Unless otherwise specified

Parameter	Symbol	Conditions	Ratings	Unit
Thermal Resistance (junction- Case)	Rth(j-c)	Tc=25°C (our ideal heat dissipation condition)*2	2.33	°C /W
Thermal Resistance (junction- atmosphere)	Rth(j-a)		47.5	°C /W

Fig.1 Switching Time Test Circuit

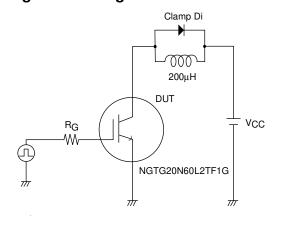
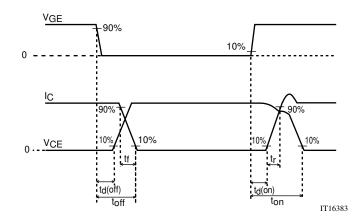
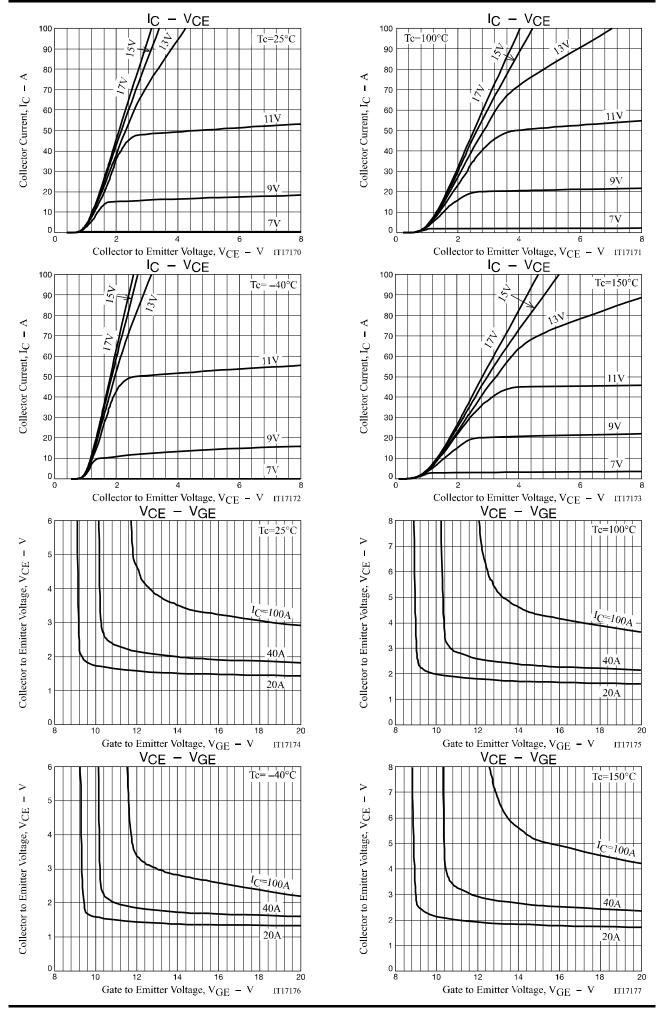
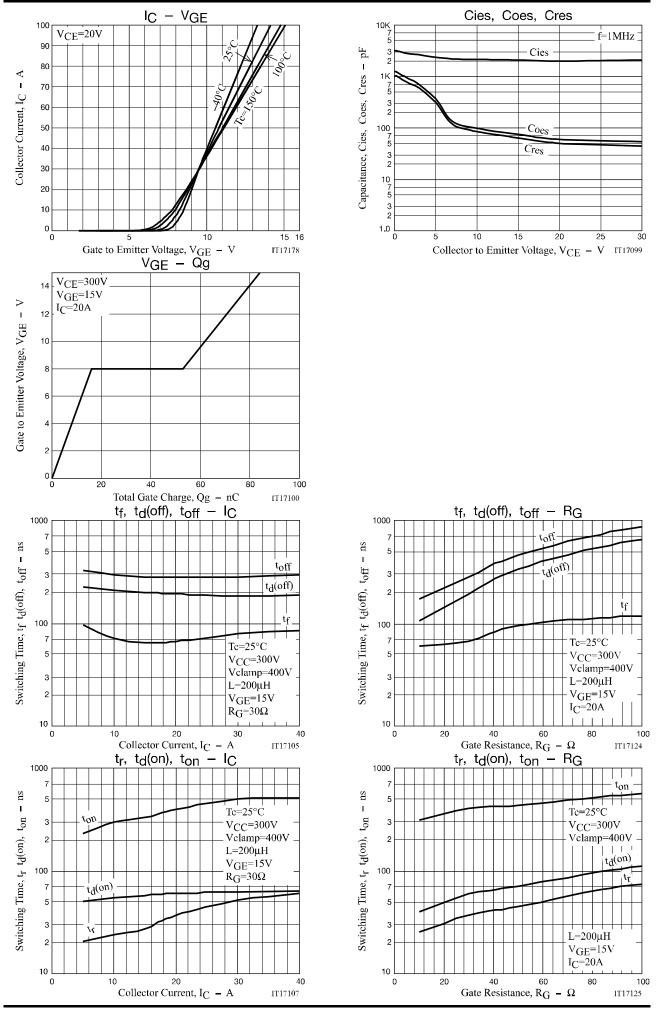
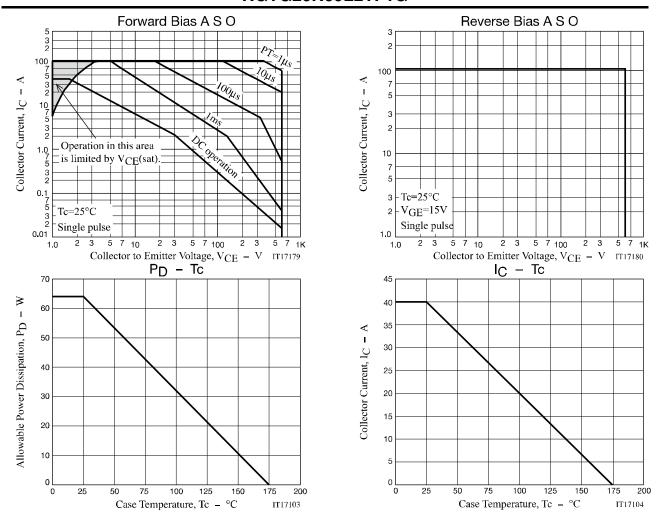


Fig.2 Timing Chart



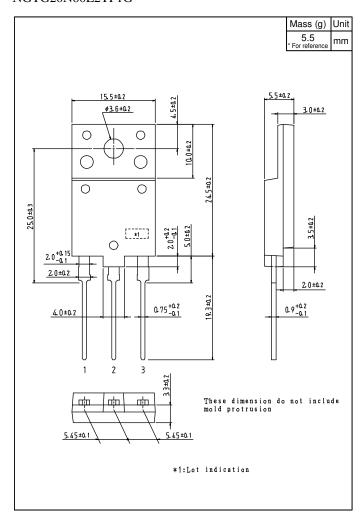






Outline Drawing

NGTG20N60L2TF1G



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